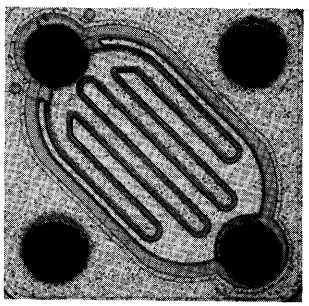
MMCFA43 (SILICON)

FLIP-CHIP
NPN HIGH-VOLTAGE
TRANSISTOR

Flip-Chip — NPN silicon annular transistor designed for applications requiring high breakdown voltages with low saturation voltages.

- Complement to PNP Type MMCFA93



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	200	Vdc
Collector-Base Voltage	V_{CB}	200	Vdc
Emitter-Base Voltage	V_{EB}	6.0	Vdc
Collector Current — Continuous	I_C	500	mAdc

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	BV_{CEO}	200	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BV_{CBO}	200	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BV_{EBO}	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 160 Vdc, I_E = 0)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	100	nAdc
DC Current Gain	h_{FE}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		25	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)		35	—	
(I_C = 30 mAdc, V_{CE} = 10 Vdc)		25	200	
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	$V_{BE(sat)}$	—	0.9	Vdc